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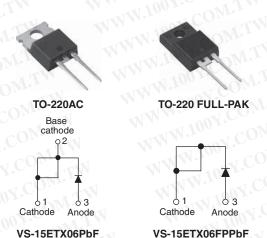
Http://www.100y.com.tw

VS-15ETX06PbF, VS-15ETX06FPPbF

Vishay Semiconductors

COMPLIANT

Ultrafast Rectifier, 15 A FRED Pt®



PRODUCT SUMMARY	MM.Ino
Package	TO-220AC, TO-220FP
I _{F(AV)}	15 A
V _R	600 V
V _F at I _F	3.2 V
t _{rr} typ.	18 ns
T _J max.	175 °C
Diode variation	Single die

FEATURES

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Benchmark ultralow forward voltage drop
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- · Designed and qualified for industrial level



State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}	11001.001.17	600	100 V
Average restified forward coursest CO	J , W	T _C = 133 °C	15	100X.Co
Average rectified forward current	I _{F(AV)}	T _C = 62 °C (FULL-PAK)	15	W.Io. CON
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	170	W.10A
Peak repetitive forward current	I _{FM}	WW TIOOY.C	30	
Operating junction and storage temperatures	T _J , T _{Stg}	MAN TOOX CO.	- 65 to 175	°C () Y

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						YOUY	
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	TW	-417	1.100 1.100	
Company valtage		I _F = 15 A	A'GOD	2.3	3.2	V	
Forward voltage	V _F	I _F = 15 A, T _J = 150 °C	47-CO	1.5	1.8	TWW.	
Davisias Ingliana aviimant	N.A.	V _R = V _R rated	00 x	0.1	50	· Wage	
Reverse leakage current	IR	T _J = 150 °C, V _R = V _R rated	1007.	40	300	μA	
Junction capacitance	C _T	V _R = 600 V	JOHY.	20	N -	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	- O.V.	8.0	-	nH	

Document Number: 94006 Revision: 28-Apr-11

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DINAMIS NESSTEN		1 ERIS 1 163 (1C =	25 °C unless other	wise speci	neu)	1	
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	100	$I_F = 1 A, dI_F/dt = 100$	A/ μ s, V _R = 30 V	COM	18	22	
Reverse recovery time	100	$I_F = 15 \text{ A}, dI_F/dt = 10$	0 A/μs, V _R = 30 V	7	20	32	
	T _{rr}	T _J = 25 °C	WWW	OUT.CO.	22	-	ns
	MW.1	T _J = 125 °C	WWW.	T.CC	52	-	
Peak recovery current		T _J = 25 °C	$I_F = 15 \text{ A}$	100 - C	2.4	-	А
	I _{RRM}	T _J = 125 °C	dI _F /dt = 200 A/μs V _R = 390 V	100.	5.1	-	A
Dana rasayan abaya	WWW	T _J = 25 °C	M. M.	160X	25	- ·	
Reverse recovery charge	Q _{rr}	T _J = 125 °C	WW WY		150	TV-	μC
Reverse recovery time	t _{rr}	M.In. COM	I _E = 15 A	111.50	37	W.	ns
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 800 \text{ A/}\mu\text{s}$	WW-100	16	1. I	Α
Reverse recovery charge	Q _{rr}	11001	V _R = 390 V	-31 10	350	WILL	nC

THERMAL - MECHANICAL SPE	CIFICATIO	ONS	MAL	1007.0	T.Mo	
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}	1100X.COM.TW	- 65	W.100Y	175	°C.
Thermal resistance,	B	TION.COM.TW	7// //	1.0	1.3	TW
junction to case (FULL-PAK)	R_{thJC}	W. COM TW	- 111	3.0	3.5	WILL
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	- 1	WW.I	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	1007.0	OM.TY
Wainta W 1001. OM.TW		M. 100 F. COM: 14	-	2.0	700	g
Weight	N	WWW.TIOOY.COM.T	_	0.07	V 180X	oz.
Mounting torque	V	MMM.100X.COM.	6.0 (5.0)	MM	12 (10)	kgf · cm (lbf · in)
WW. 100X.	Case style TO-220AC		TW	15E	TX06	77.
Marking device	WT	Case style TO-220 FULL-PAK	WIL	15ET	K06FP	101.00

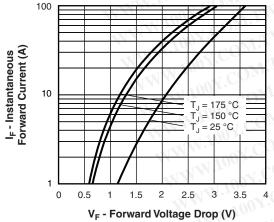


Fig. 1 - Typical Forward Voltage Drop Characteristics

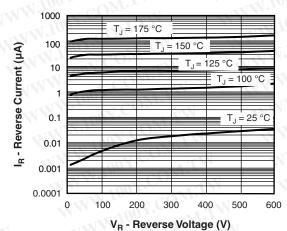


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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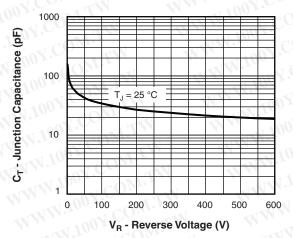


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

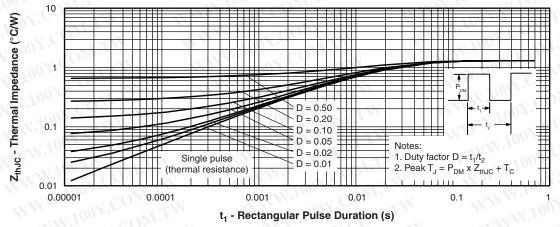


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

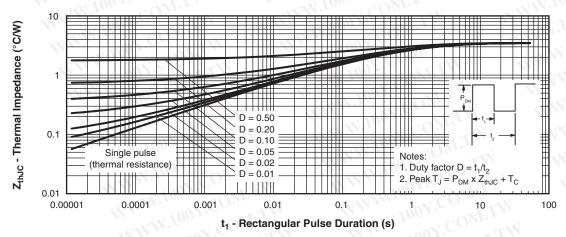
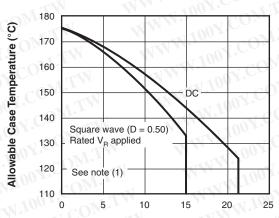


Fig. 5 - Maximum Thermal Impedance ZthJC Characteristics (FULL-PAK)

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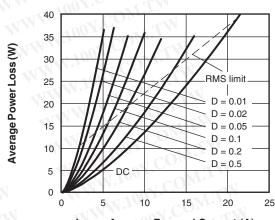
Vishay Semiconductors Ultrafast Rectifier, 15 A FRED Pt®





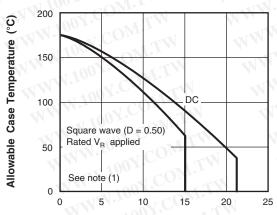
I_{F(AV)} - Average Forward Current (A)

Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current



I_{F(AV)} - Average Forward Current (A)

Fig. 8 - Forward Power Loss Characteristics



I_{F(AV)} - Average Forward Current (A)

Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

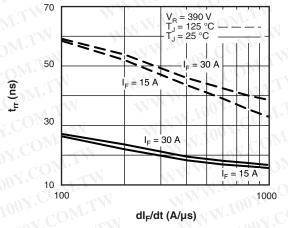


Fig. 9 - Typical Reverse Recovery Time vs. dl_F/dt

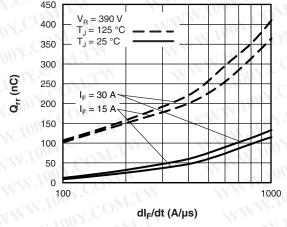


Fig. 10 - Typical Stored Charge vs. dl_F/dt

Note

(1) Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 8); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R



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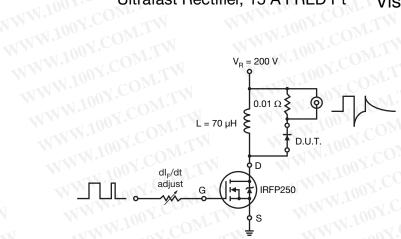
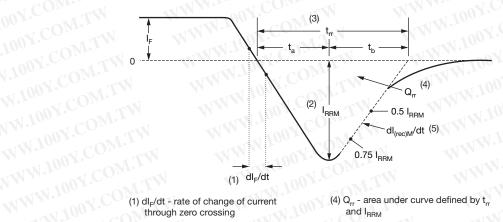


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_E/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_r and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

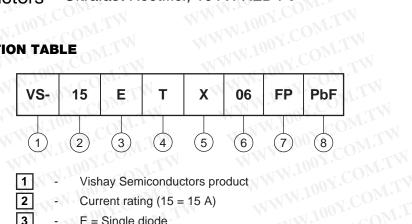
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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product 1

2 Current rating (15 = 15 A)

3 E = Single diode

4 T = TO-220, D^2PAK

5 X = Hyperfast recovery

6 Voltage rating (06 = 600 V)

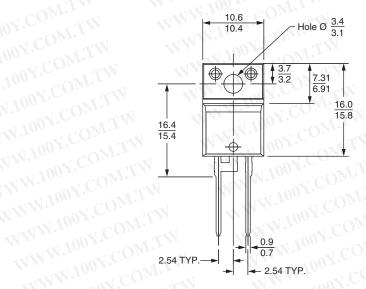
7 None = TO-220AC

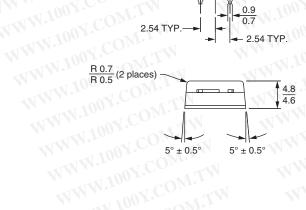
FP = TO-220 FULL-PAK

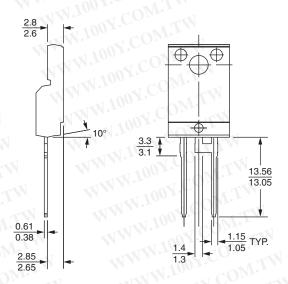
TO-220AC <u>www.vishay.com/doc?95221</u> TO-220AC FULL-PAK <u>www.vishay.com/doc?95005</u> TO-220AC <u>www.vishay.com/doc?95005</u> TO-220AC <u>www.vishay.com/doc?95224</u>	N. TOUT. COM.T.	LINKS TO RELATED DOCU	JMENTS CONTRACTOR OF THE PROPERTY OF THE PROPE	
TO-220AC FULL-PAK <u>www.vishay.com/doc?95005</u> TO-220AC www.vishay.com/doc?95224	WW 100Y.Com.T	TO-220AC	www.vishay.com/doc?95221	
TO-220AC www.vishay.com/doc?95224	nensions	TO-220AC FULL-PAK	www.vishay.com/doc?95005	
	Part marking information	TO-220AC	www.vishay.com/doc?95224	
TO-220AC FULL-PAK www.vishay.com/doc?95009		TO-220AC FULL-PAK	www.vishay.com/doc?95009	

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DIMENSIONS in millimeters







Lead assignments

Diodes

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1 + 2 - Cathode

3 - Anode

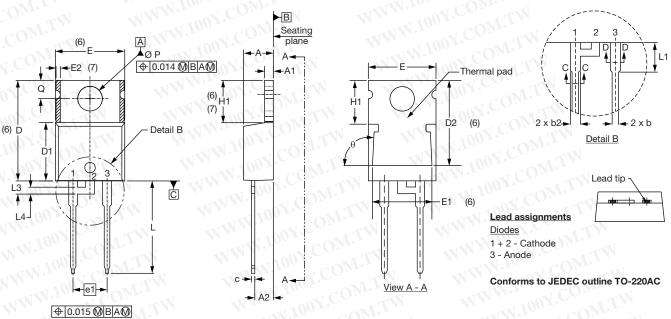
Conforms to JEDEC outline TO-220 FULL-PAK



Vishay Semiconductors

TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	M.
A1	1.14	1.40	0.045	0.055	MMM
A2	2.56	2.92	0.101	0.115	WITE
b	0.69	1.01	0.027	0.040	- TXX
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	W
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	N
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

CVMDOL	MILLIM	LIMETERS INCHES		NOTES	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E1 T	6.86	8.89	0.270	0.350	6
E2	W -	0.76	-10	0.030	7
CCe	2.41	2.67	0.095	0.105	In-
e1	4.88	5.28	0.192	0.208	OMr.
H1	6.09	6.48	0.240	0.255	6, 7
N.P	13.52	14.02	0.532	0.552	Mo.
LICO	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	N.CON
L4	0.76	1.27	0.030	0.050	2
ØP	3.54	3.73	0.139	0.147	10 7.
QOY	2.60	3.00	0.102	0.118	00 X.C.
θ	90° t	o 93°	90° t	o 93°	TOOK.C
111.100	V COD	1		TAT WWW	· Jus

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- 3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline





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